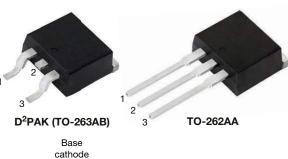
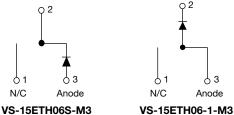
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VS-15ETH06S-M3, VS-15ETH06-1-M3

Vishay Semiconductors

Hyperfast Rectifier, 15 A FRED Pt[®]





3

PRIMARY CHARACTERISTICS								
I _{F(AV)} 15 A								
V _R	600 V							
V _F at I _F	1.3 V							
t _{rr} (typ.)	22 ns							
T _J max.	175 °C							
Package	D ² PAK (TO-263AB), TO-262AA							
Circuit configuration	Single							

FEATURES

- · Hyperfast recovery time
- · Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature
- · Single die center tap module
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Peak repetitive reverse voltage	V _{RRM}		600	V			
Average rectified forward current	I _{F(AV)}	T _C = 140 °C	15				
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	120	А			
Peak repetitive forward current	I _{FM}		30				
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-			
Forward voltage	V	I _F = 15 A	-	1.8	2.2	V		
Forward voltage	V _F	I _F = 15 A, T _J = 150 °C	-	1.3	1.6			
Reverse leakage current	1-	$V_R = V_R$ rated	-	0.2	50	μA		
neverse leakage current	IR	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	30	500	μΑ		
Junction capacitance	CT	V _R = 600 V	-	20	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

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Document Number: 96301

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FREE



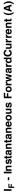
VS-15ETH06S-M3, VS-15ETH06-1-M3

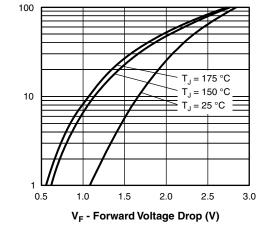
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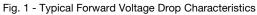
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DYNAMIC RECOVERY	CHARACT	ERISTICS (T _C = 25	5 °C unless otherwis	e specifie	ed)			
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
		I _F = 1 A, dI _F /dt = 1	00 A/µs, V _R = 30 V	-	22	30		
Reverse recovery time	+	I _F = 15 A, dI _F /dt =	100 A/µs, V _R = 30 V	-	28	35	ns	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	29	-	115	
		T _J = 125 °C			-	75	-	
Deels receiver a current	1	T _J = 25 °C	$I_F = 15 A$		3.5	-	A	
Peak recovery current	IRRM	T _J = 125 °C	$V_{\rm R} = 390 {\rm V}$	-	7	-		
	0	T _J = 25 °C		-	57	-		
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	300	-	μC	
Reverse recovery time	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	-	ns					
Peak recovery current	I _{RRM}	T _J = 125 °C	dI _F /dt = 800 A/µs	-	20	-	А	
Reverse recovery charge	Q _{rr}		V _R = 390 V	-	580	-	nC	

THERMAL - MECHANIC	CAL SPEC	IFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case per leg	R _{thJC}		-	1.0	1.3	
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-	
W/oight			-	2.0	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking davias		Case style D ² PAK (TO-263AB)		15ET	H06S	
Marking device		Case style TO-262AA		15ET	H06-1	







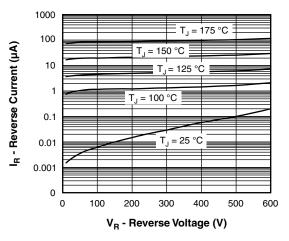


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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VS-15ETH06S-M3, VS-15ETH06-1-M3

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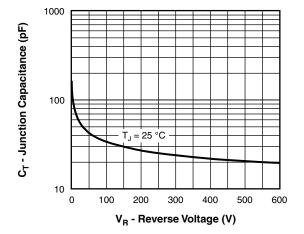


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

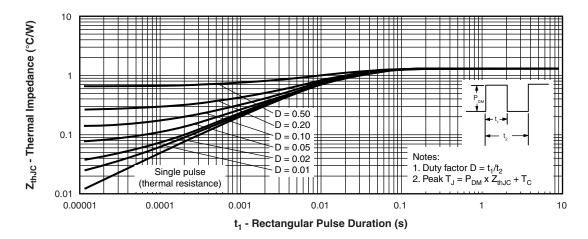
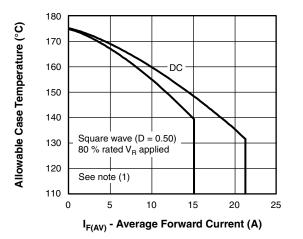
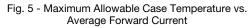


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}/D$) (see fig. 6); Pd_{REV} = inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = rated V_R

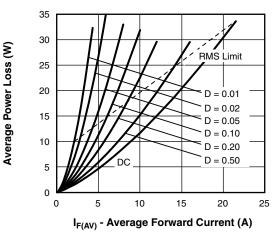


Fig. 6 - Forward Power Loss Characteristics

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VS-15ETH06S-M3, VS-15ETH06-1-M3



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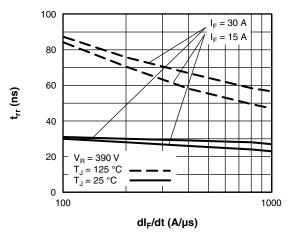


Fig. 7 - Typical Reverse Recovery vs. dl_F/dt

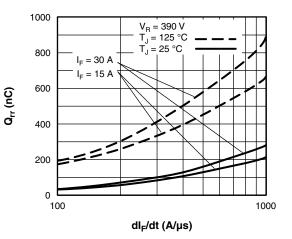


Fig. 8 - Typical Stored Charge vs. dl_F/dt

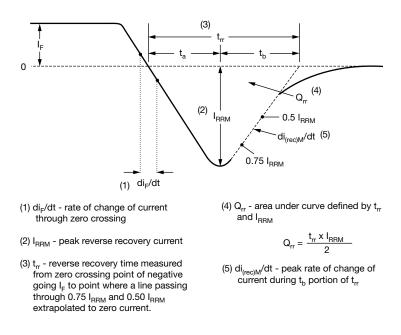
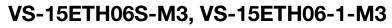


Fig. 9 - Reverse Recovery Waveform and Definitions



Vishay Semiconductors

ORDERING INFORMATION TABLE

www.vishay.com

SHA)

Device code	vs-	15	Е	т	н	06	S	TRL	-M3
		(2)	(3)	4	(5)	(6)	(7)	(8)	(9)
	1 -		-	niconduo ng (15 A		oduct			
	3 - 4 -		single o	liode , D ² PAł	((TO-2	63AB)			
	5 -			st rectif		,			
	6 -		-	ng (06 =	,)			
	7 -		= D ² PA = TO-2	K (TO-2	63AB)				
	8 -			ozaa be (50 p	oieces)				
	_	• TI	RL = tap	e and re	eel (left	oriented	l, for D ²	² PAK (T	O-263A
	_	• TI	R = tap	be and r	eel (righ	nt orient	ed, for l	D ² PAK ((TO-263
	9 -	Env	ironmer	ntal digit:					

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION					
VS-15ETH06S-M3	50	Antistatic plastic tubes					
VS-15ETH06STRR-M3	800	13" diameter plastic tape and reel					
VS-15ETH06STRL-M3	800	13" diameter plastic tape and reel					
VS-15ETH06-1-M3	50	Antistatic plastic tubes					

	LINKS TO RELATED DOCUMENTS								
Dimensions	D ² PAK (TO-263AB)	www.vishay.com/doc?96164							
Dimensions	TO-262	www.vishay.com/doc?96165							
Dest medice information	D ² PAK (TO-263AB)	www.vishay.com/doc?95444							
Part marking information	TO-262	www.vishay.com/doc?95443							
Packaging information		www.vishay.com/doc?96424							
SPICE model		www.vishay.com/doc?96617							

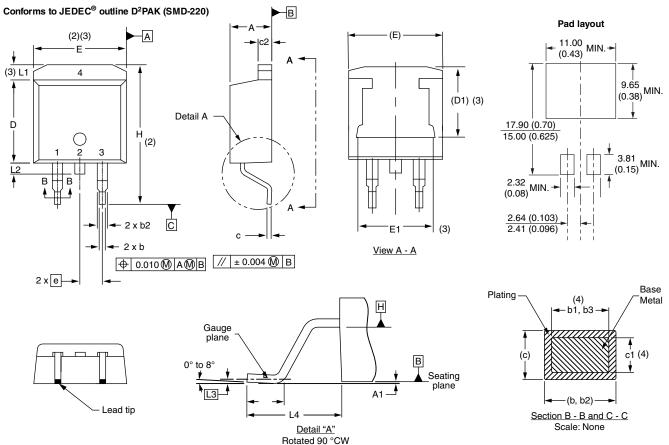
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D²PAK

DIMENSIONS in millimeters and inches

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ISHA





SYMBOL	MILLIM	MILLIMETERS		HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
A	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STNIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	BSC	0.100) BSC	
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25	BSC	0.010	BSC	
L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 13-Jul-17

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Document Number: 96164

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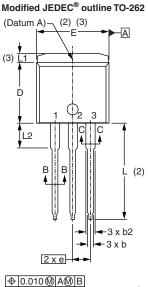
Outline Dimensions

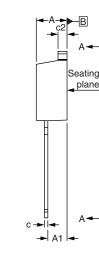


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TO-262AA

DIMENSIONS in millimeters and inches



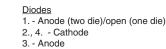


D1 (3) (3) Section A - A Base (4) Plating b1. b3 metal ≰ c1 (4) -(b, b2)-Section B - B and C - C Scale: None

E

010	(M) A	.@/E	3		
_				_	
	math	math.	mark		





Lead assignments

SYMBOL	MILLIN	METERS	INC	INCHES		
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	2.03	3.02	0.080	0.119		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	
D1	6.86	8.00	0.270	0.315	3	
E	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54	BSC	0.100) BSC		
L	13.46	14.10	0.530	0.555		
L1	-	1.65	-	0.065	3	
L2	3.56	3.71	0.140	0.146		

Notes

 ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the second flash include mold flash. the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Controlling dimension: inches

(6) Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)

Revision: 30-Nov-17

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